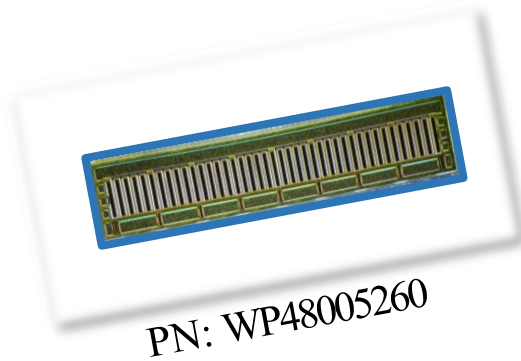




WP48005260

260W, 48V GaN HEMT Die



The WP48005260 is a 260W gallium nitride (GaN) High Electron Mobility Transistor (HEMT). This GaN HEMT is a wideband transistor optimized for 3.5GHz operation in a user-friendly device for high bandwidth applications. Gallium nitride (GaN) HEMT is a device optimized for 5G. GaN HEMT resistance is only 1/10 that of silicon transistors, making it capable of switching frequencies faster for greater energy efficiency.

Features

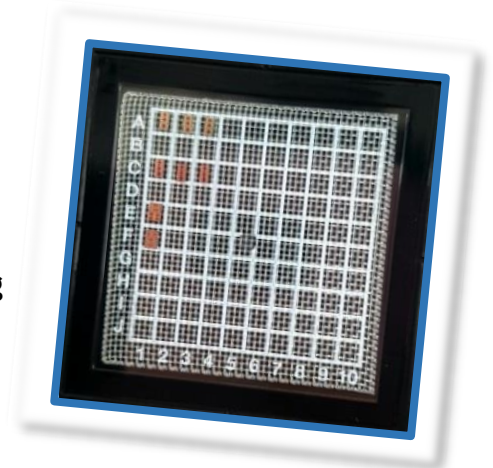
- Up to 5 GHz Operation
- 14.0 dB Typical Small Signal Gain @ 3.5 GHz
- 260 W Typical Psat @3.5GHz
- 48V Operation
- High Breakdown Voltage
- High Breakdown Voltage
- High Efficiency
- Reliability Monitoring Supporting

Applications

- U/VHF Amplifiers
- Broadband Amplifiers
- Base Station Communications
- Drone, UAV
- WiMAX, LTE, WCDMA, GSM
- WPT, V2X
- Radar application

Packaging Information

- Bare die are shipped in Wafer-level with Expander Ring or Gel-Pak® containers.
- Possible UV Curing for Wafer-level with dicing saw



Absolute Maximum Ratings (not simultaneous) at 25 °C

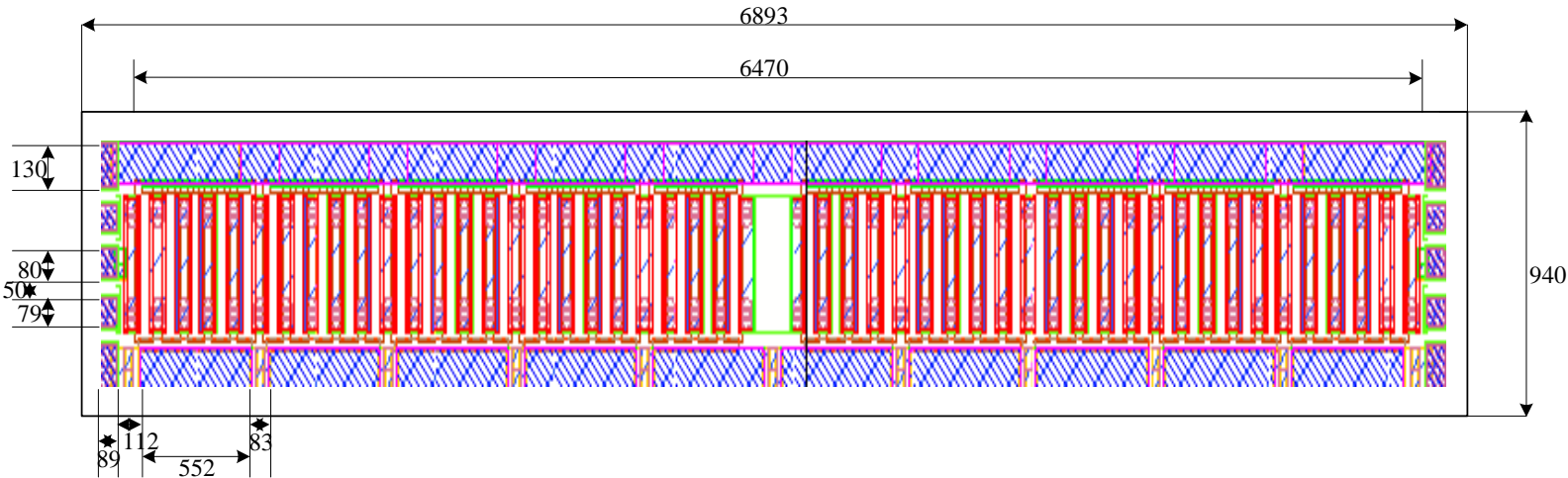
Parameter	Parameter	Typical Value	Units	Conditions
Threshold voltage @ Id=1mA/mm, Vd=10V	V _{to}	-3.4	V	25°C
Breakdown voltage @ Id=1mA/mm	V _{DG}	160	V	25°C
Drain-source current, Id @ Vd=10V, Vg=0	I _{dss}	800	mA/mm	25°C
Operating Junction Temperature	T _J	225	°C	
Storage Temperature	T _{STG}	-65, +150	°C	
Thermal Resistance, Junction to Case (packaged)	R _{θJC}		°C/W	
Thermal Resistance, Junction to Case (die only)	R _{θJC}		°C/W	
Mounting Temperature (30 seconds)	T _S	320	°C	30 seconds

Electrical Characteristics (Frequency = 3.5 GHz unless otherwise stated; TC = 25 °C)

Parameter	Parameter	Typical Value	Units	Conditions
DC Characteristics				
Ohmic contact resistance	RC	0.3	Ohm-mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
Max. trans-conductance, @ Vd=10V, Vg=-4V ~ -1V (1X125µm device)	GM_PEAK	290	mS/mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
RF Characteristics				
Small Signal Gain	G _{SS}	>12	dB	V _{DD} =48V, I _{DQ} =1320mA
Saturated Power Output	P _{SAT}	260	W	V _{DD} =48V, I _{DQ} =1320mA
Drain Efficiency	η	>55	%	V _{DD} =48V, I _{DQ} =1320mA
Intermodulation Distortion	IM3	<-30	dBc	V _{DD} =48V, I _{DQ} =1320mA
Output Mismatch Stress	VSWR	10:1	ψ	



DIE Dimensions (units in microns)



Overall die size 6893 x 940 (+0/-50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

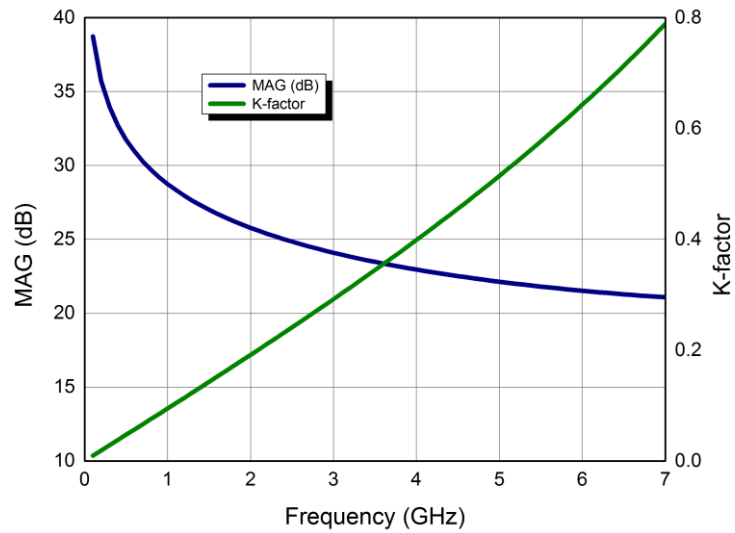
- Recommended solder is AuSn (80/20) solder. Refer to Wavepia's guide for the Eutectic Die Bond Procedure
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.



Typical Performance

Simulated Maximum Available Gain (MAG) and K Factor of the WP48005260

$$V_{DD} = 48 \text{ V}, I_{DQ} = 1320 \text{ mA}$$

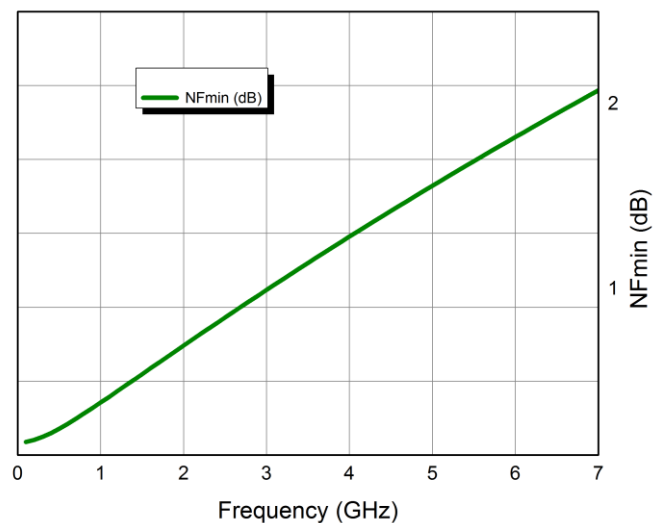


Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Performance

Simulated Minimum Noise Figure of the WP48005260

$$V_{DD} = 48 \text{ V}, I_{DQ} = 1320 \text{ mA}$$





Typical Die S-Parameters

(Small Signal, $V_{DS} = 48\text{ V}$, $I_{DQ} = 1320\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
100MHz	0.976668	-155.255	28.3582	100.5665	0.003799	10.72547	0.840368	-175.964
200MHz	0.975938	-167.452	14.40755	92.87321	0.00386	3.19119	0.848269	-177.545
300MHz	0.975869	-171.584	9.618342	89.17357	0.003865	-0.34943	0.850309	-177.927
400MHz	0.975928	-173.649	7.203394	86.5022	0.003858	-2.86173	0.851641	-177.997
500MHz	0.976046	-174.884	5.746818	84.25091	0.003846	-4.9539	0.85292	-177.945
600MHz	0.976204	-175.702	4.771307	82.21682	0.003831	-6.82879	0.854303	-177.834
700MHz	0.976395	-176.282	4.071318	80.3138	0.003812	-8.57252	0.855836	-177.694
800MHz	0.976616	-176.715	3.543825	78.49963	0.00379	-10.2273	0.857528	-177.54
900MHz	0.976862	-177.049	3.131511	76.75155	0.003765	-11.8159	0.859378	-177.38
1000MHz	0.977131	-177.314	2.79996	75.05647	0.003738	-13.3513	0.861377	-177.219
1100MHz	0.977422	-177.53	2.52726	73.40655	0.003709	-14.8415	0.863513	-177.062
1200MHz	0.977731	-177.709	2.298799	71.7969	0.003677	-16.2912	0.865772	-176.909
1300MHz	0.978057	-177.86	2.104461	70.22443	0.003644	-17.7035	0.86814	-176.764
1400MHz	0.978397	-177.99	1.937018	68.68713	0.003608	-19.0805	0.870601	-176.626
1500MHz	0.978749	-178.103	1.79117	67.18368	0.003572	-20.4235	0.873142	-176.498
1600MHz	0.979112	-178.202	1.662938	65.71317	0.003533	-21.7332	0.875746	-176.379
1700MHz	0.979483	-178.29	1.54928	64.27495	0.003493	-23.0105	0.878401	-176.269
1800MHz	0.97986	-178.37	1.447829	62.86855	0.003452	-24.2556	0.881094	-176.17
1900MHz	0.980242	-178.442	1.356711	61.49357	0.00341	-25.4691	0.883811	-176.079
2000MHz	0.980627	-178.508	1.274428	60.14964	0.003368	-26.6512	0.886541	-175.999
2100MHz	0.981013	-178.569	1.199763	58.83641	0.003324	-27.8024	0.889274	-175.927
2200MHz	0.9814	-178.625	1.131718	57.55354	0.00328	-28.9228	0.892001	-175.865
2300MHz	0.981785	-178.679	1.069468	56.30065	0.003235	-30.013	0.894711	-175.811
2400MHz	0.982169	-178.729	1.01232	55.07733	0.00319	-31.0732	0.897399	-175.765
2500MHz	0.982549	-178.776913	0.959693	53.88315	0.003145	-32.1039	0.900056	-175.728
2600MHz	0.982924	-178.822512	0.91109	52.71765	0.003099	-33.1055	0.902677	-175.697
2700MHz	0.983295	-178.866236	0.866089	51.58033	0.003054	-34.0785	0.905256	-175.673
2800MHz	0.98366	-178.908336	0.824323	50.47068	0.003008	-35.0235	0.907791	-175.656
2900MHz	0.984019	-178.949021	0.785477	49.38814	0.002963	-35.9409	0.910275	-175.645
3000MHz	0.984372	-178.988467	0.749273	48.33215	0.002918	-36.8312	0.912708	-175.64
3100MHz	0.984717	-179.02682	0.71547	47.30213	0.002873	-37.6951	0.915086	-175.64
3200MHz	0.985054	-179.064205	0.683854	46.29748	0.002828	-38.5332	0.917407	-175.645
3300MHz	0.985384	-179.100725	0.654237	45.31758	0.002784	-39.3459	0.919671	-175.654
3400MHz	0.985707	-179.136467	0.626451	44.36183	0.00274	-40.134	0.921875	-175.667
3500MHz	0.986021	-179.171507	0.600346	43.4296	0.002696	-40.898	0.924021	-175.684
3600MHz	0.986327	-179.205906	0.575789	42.52026	0.002653	-41.6384	0.926106	-175.704
3700MHz	0.986624	-179.23972	0.552659	41.6332	0.00261	-42.3561	0.928133	-175.728
3800MHz	0.986914	-179.272993	0.530848	40.76779	0.002568	-43.0514	0.9301	-175.754
3900MHz	0.987196	-179.306	0.510258	39.92342	0.002526	-43.725	0.932008	-175.783

Contact WAVEPIA to receive this s-parameter file in “.s2p” format at platune@wavepia.com

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